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# BLL6H1214-500; BLL6H1214LS-500 LDMOS L-band radar power transistor

Rev. 4 — 1 September 2015



#### **Product profile** 1.

### 1.1 General description

500 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

#### Test information Table 1.

Typical RF performance at  $T_{case} = 25 \ ^{\circ}C$ ;  $t_p = 300 \ \mu s$ ;  $\delta = 10 \ ^{\circ}$ ;  $I_{Da} = 150 \ mA$ ; in a class-AB production test circuit.

Test signal	f	V <sub>DS</sub>	PL	Gp	η <sub>D</sub>	tr	t <sub>f</sub>
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	1.2 to 1.4	50	500	17	50	20	6

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

#### 1.3 Applications

L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range

# BLL6H1214-500; BLL6H1214LS-500

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### 2. Pinning information

Pin	Description	Simplified outlin	e Graphic symbol
BLL6H1	214-500 (SOT539A)		
1	drain1		
2	drain2		
3	gate1		
4	gate2	3 4	5
5	source	<u>[1]</u>	

BLL6H1214LS-500 (SOT539B)1drain12drain23gate14gate25source11 $2 = 10^{-1}$ 

[1] Connected to flange.

### 3. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BLL6H1214-500	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A		
BLL6H1214LS-500	-	earless flanged balanced ceramic package; 4 leads	SOT539B		

### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	100	V
V <sub>GS</sub>	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

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### 5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
BLL6H12	214-500			
Z <sub>th(j-c)</sub>	transient thermal impedance from	T <sub>case</sub> = 85 °C; P <sub>L</sub> = 500 W		
	junction to case	$t_p$ = 100 $\mu$ s; $\delta$ = 10 %	0.07	K/W
		$t_p$ = 200 $\mu$ s; $\delta$ = 10 %	0.08	K/W
		$t_p$ = 300 µs; $\delta$ = 10 %	0.1	K/W
		$t_p$ = 100 $\mu$ s; $\delta$ = 20 %	0.1	K/W
BLL6H12	214LS-500			
Z <sub>th(j-c)</sub>	transient thermal impedance from	T <sub>case</sub> = 85 °C; P <sub>L</sub> = 500 W		
	junction to case	$t_p$ = 100 $\mu$ s; $\delta$ = 10 %	0.046	K/W
		$t_p$ = 200 $\mu$ s; $\delta$ = 10 %	0.059	K/W
		$t_p$ = 300 $\mu$ s; $\delta$ = 10 %	0.069	K/W
		$t_p$ = 100 $\mu$ s; $\delta$ = 20 %	0.064	K/W

### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25 \ ^{\circ}C$ ; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS}$ = 0 V; I <sub>D</sub> = 2.7 mA	100	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; I <sub>D</sub> = 270 mA	1.3	1.8	2.2	V
I <sub>DSS</sub>	drain leakage current	$V_{GS}$ = 0 V; $V_{DS}$ = 50 V	-	-	1.4	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	32	42	-	A
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 11 V; $V_{DS}$ = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 270 mA	1.7	3	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 9.5 A$	-	100	164	mΩ

#### Table 7. RF characteristics

Test signal: pulsed RF;  $t_p = 300 \ \mu s$ ;  $\delta = 10 \ \%$ ; RF performance at  $V_{DS} = 50 \ V$ ;  $I_{Dq} = 150 \ mA$ ;  $T_{case} = 25 \ ^{\circ}C$ ; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PL	output power		500	-	-	W
V <sub>DS</sub>	drain-source voltage	P <sub>L</sub> = 500 W	-	-	50	V
G <sub>p</sub>	power gain	P <sub>L</sub> = 500 W	15	17	-	dB
RL <sub>in</sub>	input return loss	P <sub>L</sub> = 500 W	-	-10	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	600	-	W
η <sub>D</sub>	drain efficiency	P <sub>L</sub> = 500 W	45	50	-	%

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#### Table 7. RF characteristics ... continued

Test signal: pulsed RF;  $t_p = 300 \ \mu s$ ;  $\delta = 10 \ \%$ ; RF performance at  $V_{DS} = 50 \ V$ ;  $I_{Dq} = 150 \ mA$ ;  $T_{case} = 25 \ \%$ ; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P <sub>droop(pulse)</sub>	pulse droop power	P <sub>L</sub> = 500 W	-	0	0.3	dB
t <sub>r</sub>	rise time	P <sub>L</sub> = 500 W	-	20	50	ns
t <sub>f</sub>	fall time	P <sub>L</sub> = 500 W	-	6	50	ns

### 7. Test information

#### 7.1 Ruggedness in class-AB operation

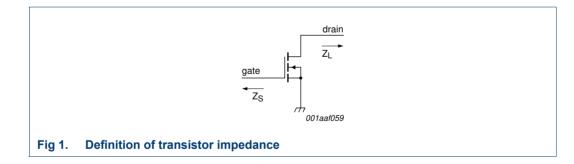
The BLL6H1214-500 and BLL6H1214LS-500 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dg}$  = 150 mA;  $P_L$  = 500 W;  $t_p$  = 300 µs;  $\delta$  = 10 %.

#### 7.2 Impedance information

#### Table 8. Typical impedance

Typical values per section unless otherwise specified.

f	Z <sub>S</sub>	ZL
(GHz)	(Ω)	(Ω)
1.2	1.268 – j2.623	2.987 – j1.664
1.3	2.193 – j2.457	2.162 – j1.326
1.4	2.359 – j2.052	1.604 – j1.887



#### 7.3 Test circuit

#### Table 9. List of components

For test circuit see Figure 2.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	22 μF, 35 V	
C2	multilayer ceramic chip capacitor	51 pF	[1]
C3, C4	multilayer ceramic chip capacitor	100 pF	<u>[1]</u>
C5, C11, C12	multilayer ceramic chip capacitor	1 nf	[2]
C6	multilayer ceramic chip capacitor	47 pF	[1]
C7, C8, C10	multilayer ceramic chip capacitor	51 pF	[3]

### LDMOS L-band radar power transistor

#### Table 9. List of components ...continued

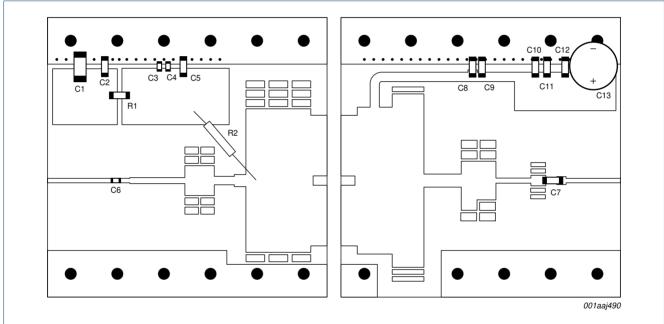
For test circuit see Fi	iaure	2.
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Component	Description	Value	Remarks
C9	multilayer ceramic chip capacitor	100 pF	<u>[3]</u>
C13	electrolytic capacitor	10 μF, 63 V	
R1	SMD resistor	56 Ω	0603
R2	metal film resistor	51 Ω	

[1] American Technical Ceramics type 100A or capacitor of same quality.

[2] American Technical Ceramics type 100B or capacitor of same quality.

[3] American Technical Ceramics type 800B or capacitor of same quality.



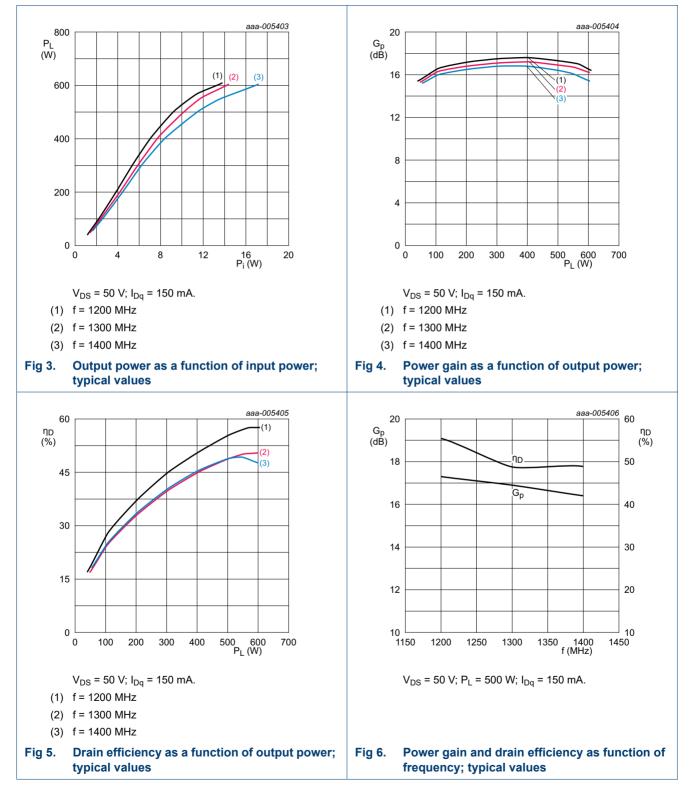
Printed-Circuit Board (PCB): Duroid 6006;  $\varepsilon_r$  = 6.15 F/m; thickness = 0.64 mm; thickness copper plating = 35  $\mu$ m. See Table 9 for a list of components.

Fig 2. Component layout for class-AB production test circuit

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### 7.4 RF performance graphs

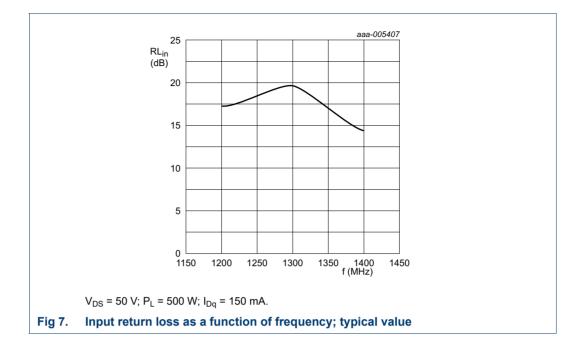
### 7.4.1 Performance curves measured with $\delta$ = 10 %, t<sub>p</sub> = 300 µs and T<sub>h</sub> = 25 °C



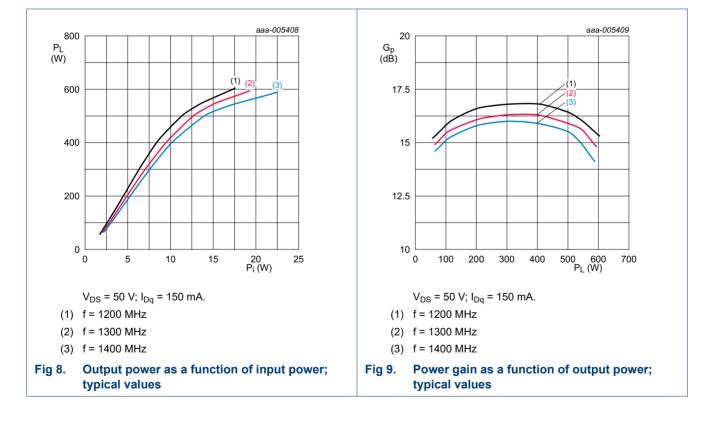
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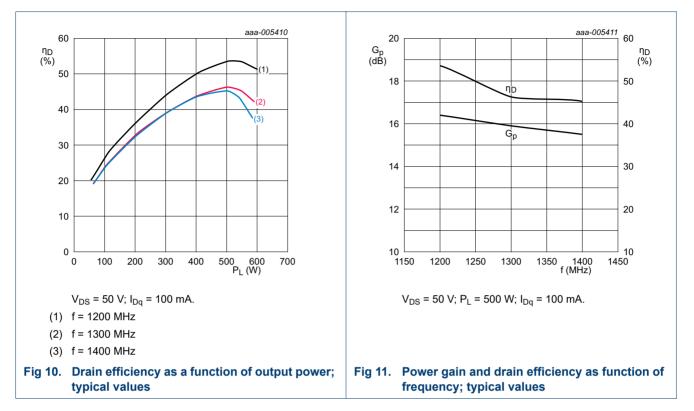


### 7.4.2 Performance curves measured with $\delta$ = 10 %, t<sub>p</sub> = 300 µs and T<sub>h</sub> = 65 °C

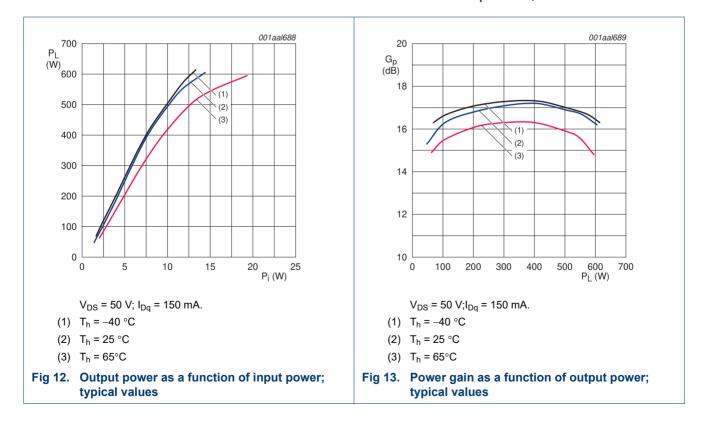


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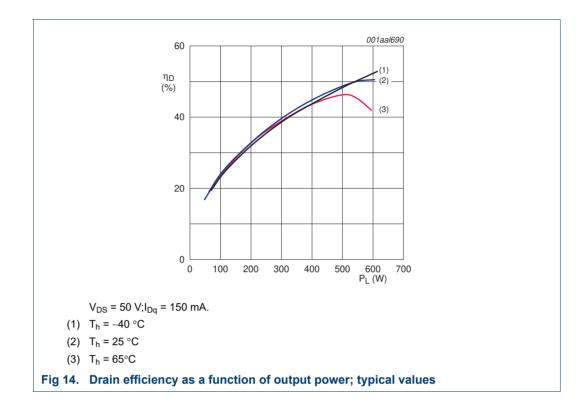


### 7.4.3 Performance curves measured with $\delta$ = 10 %, $t_p$ = 300 $\mu s$ and f = 1300 MHz

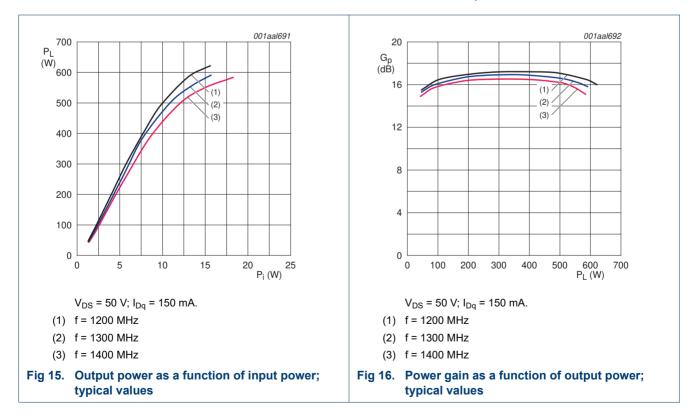


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### 7.4.4 Performance curves measured with $\delta$ = 20 %, $t_p$ = 500 $\mu s$ and $T_h$ = 25 °C



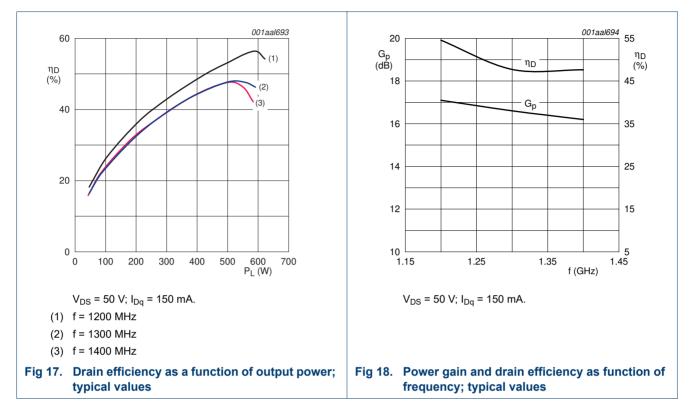
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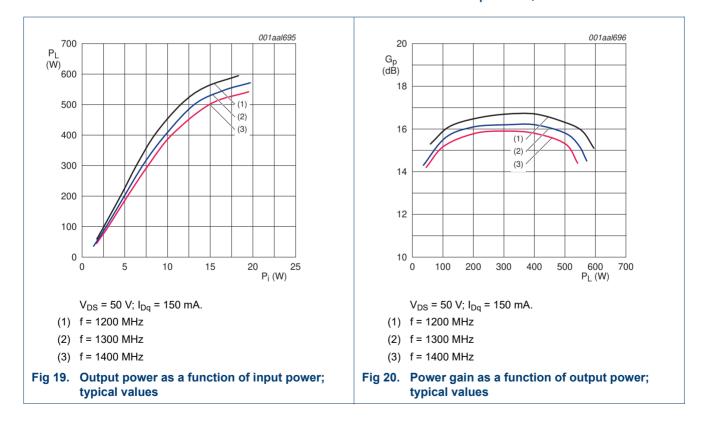
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### 7.4.5 Performance curves measured with $\delta$ = 20 %, t<sub>p</sub> = 500 µs and T<sub>h</sub> = 65 °C



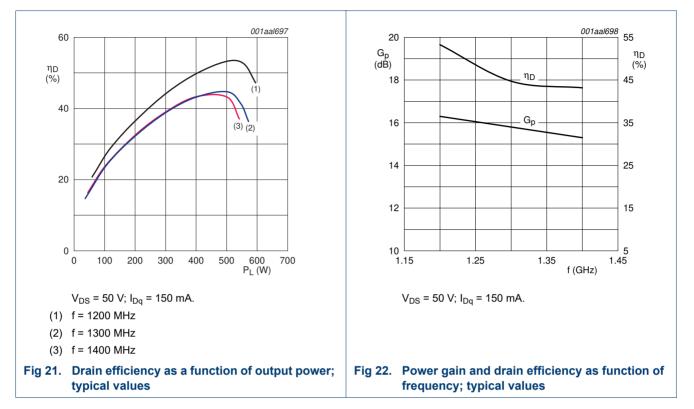
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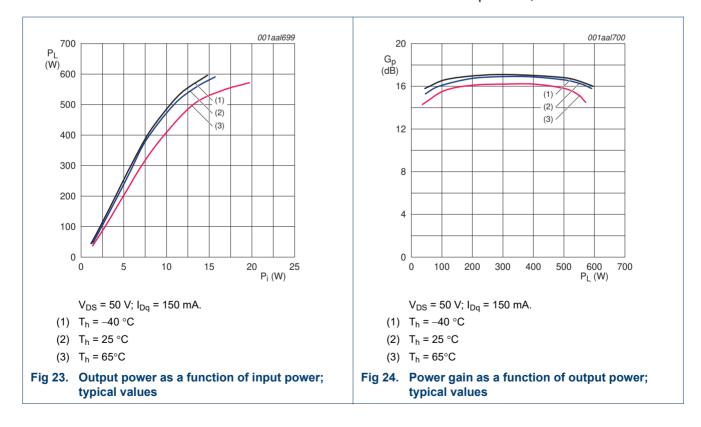
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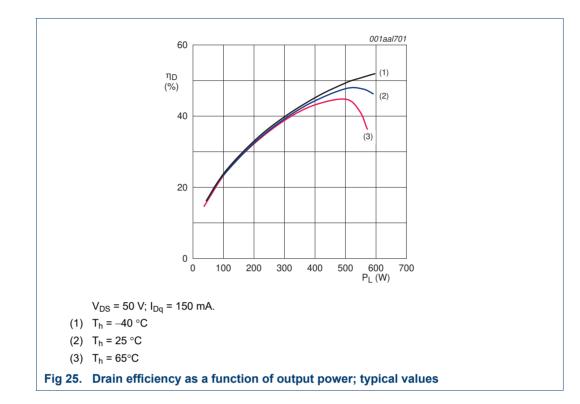
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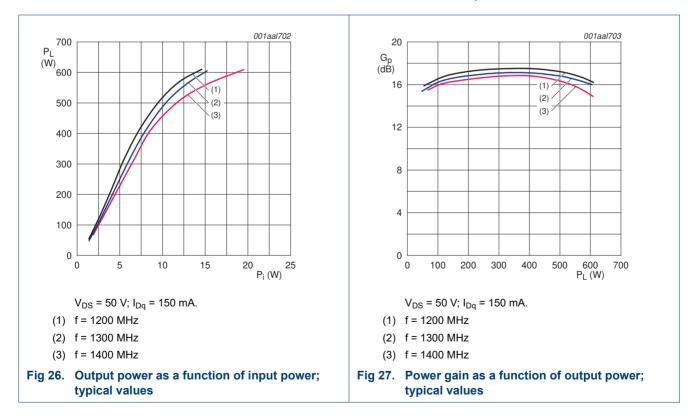
### 7.4.6 Performance curves measured with $\delta$ = 20 %, $t_p$ = 500 $\mu s$ and f = 1300 MHz



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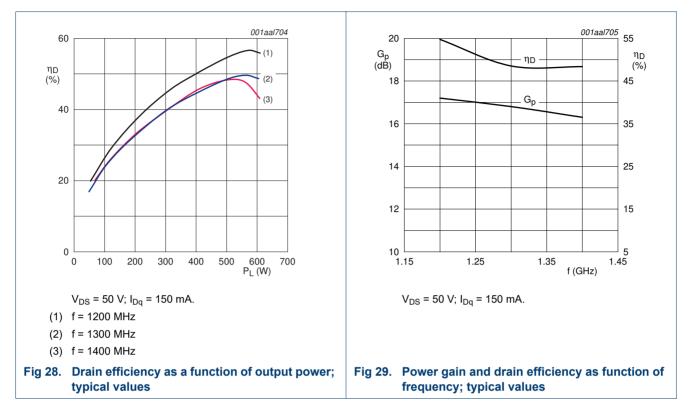


### 7.4.7 Performance curves measured with $\delta$ = 10 %, $t_p$ = 1 ms and $T_h$ = 25 °C

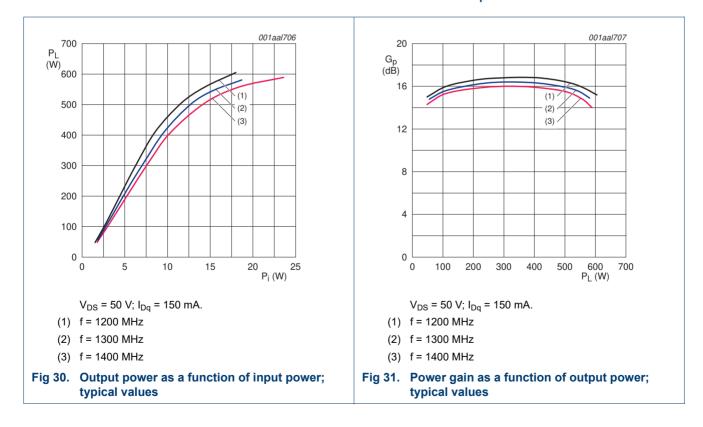


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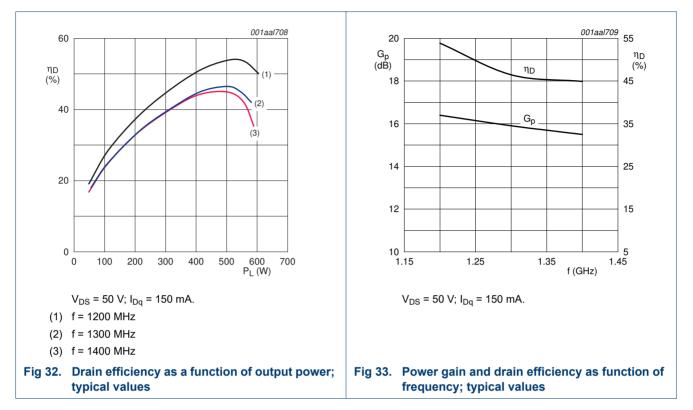


### 7.4.8 Performance curves measured with $\delta$ = 10 %, t<sub>p</sub> = 1 ms and T<sub>h</sub> = 65 °C

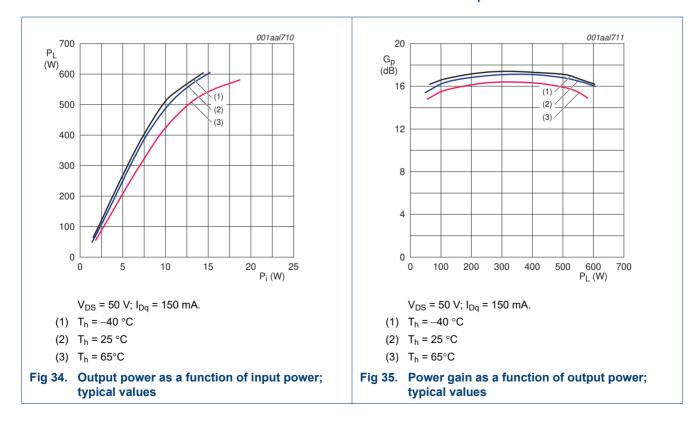


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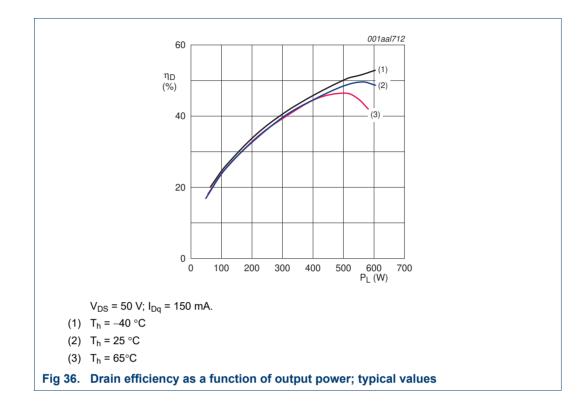
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### 7.4.9 Performance curves measured with $\delta$ = 10 %, t<sub>p</sub> = 1 ms and f = 1300 MHz



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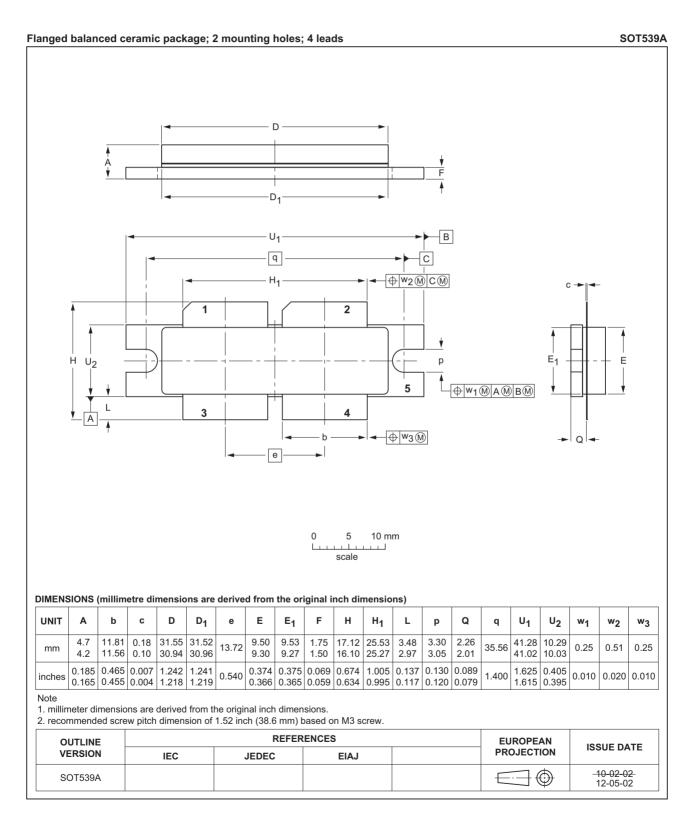
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### 8. Package outline

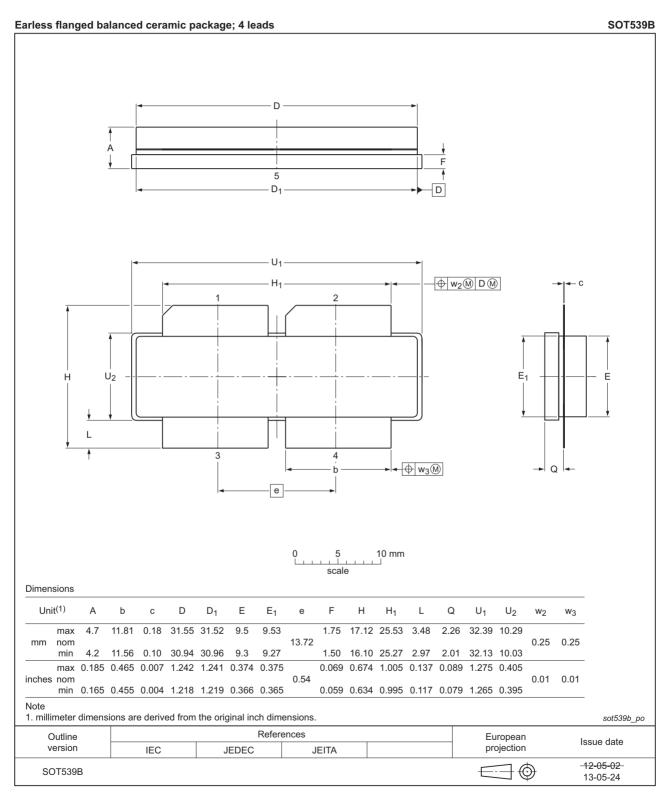


#### Fig 37. Package outline SOT539A

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#### Fig 38. Package outline SOT539B

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### 9. Handling information

equivalent standards.

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices. Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or

### 10. Abbreviations

Table 10. Abbreviations				
Acronym	Description			
ESD	ElectroStatic Discharge			
L-band	Long wave Band			
LDMOS	Laterally Diffused Metal-Oxide Semiconductor			
SMD	Surface Mounted Device			
VSWR	Voltage Standing-Wave Ratio			

### 11. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLL6H1214-500_1214LS-500#4	20150901	Product data sheet		BLL6H1214-500_121 4LS-500 v.3	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
BLL6H1214-500_1214LS-500 v.3	20130805	Product data sheet	-	BLL6H1214-500 v.2	
BLL6H1214-500 v.2	20100401	Product data sheet	-	BLL6H1214-500 v.1	
BLL6H1214-500 v.1	20090120	Objective data sheet	-	-	

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### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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